arXiv:1606.06203v2 [physics.optics] 6 Oct 2016

Application of the generalized Kirchhoff's law to calculation of photoluminescence spectra of one-dimensional photonic crystals

M. M. Voronov*
Ioffe Institute, St. Petersburg, Russia
(Dated: October 7, 2016)

The approach based on the generalized Kirchhoff's law for calculating photoluminescence (PL) spectra of one-dimensional (1D) multi-layered structures, in particular, 1D photonic crystals has been developed. It is valid in the local thermodynamic equilibrium approximation and leads to simple and explicit expression for the photoluminescence intensity. In the framework of the present theory the analytical expression for the spontaneous emission intensity enhancement factor (IEF) for a 1D photonic crystal has been derived. It takes a particularly simple form in the case of a sufficiently large number of the layers and is well suitable for analysis; in particular, it explains the difference in the emission intensity at frequencies near different edges of photonic band-gaps (PBGs), where the intensity is relatively high, and specificity of suppression of the emission in a given frequency range. Also, the developed approach is discussed in connection with the standard method using the Fermi's golden rule and the concept of the local density of (optical) states (LDOS).

I. INTRODUCTION

The theory of light emission from microstructures has been described in many books and reviews, see, e.g., [1 and 2]. The principle difference in the calculation methods is related to the electromagnetic field quantization, which in most experiments on luminescence is not apparent. This situation corresponds to the so-called weak-coupling regime where the atom-cavity coupling constant, g, is much less than the cavity decay rate, κ, and the dipole decay rate, γ, which are due to two energy-loss mechanisms. The opposite case where the dipole-cavity interaction dominates over the dissipative processes and zero-point energy must be taken into account is the strong-coupling regime [3]. It corresponds to the condition $g \gtrsim \kappa,\gamma$ and is realized in high quality-factor microcavities and photonic crystals within the photonic band-gap region making spontaneous emission a reversible process and in the case of $g >> \kappa,\gamma$ (the quantum-coherent coupling regime) leading to Rabi oscillations [4]. The weak-coupling regime is characterized by an exponential decay of the light intensity, but with a different decay rate compared to that in free space (the Purcell effect [5]), which is perfectly realized, for instance, for a 1D photonic crystal with a moderate number of periods. As a rule, one-dimensional structures, including photonic crystals and microcavities, allow a much simpler theoretical description of their optical properties than two- and three-dimensional systems, leading to explicit analytical expressions; in particular, these were obtained in [6–10], where the light emission was studied. In papers [11–13] the approach using the concept of the electromagnetic density of modes in 1D periodic structures was developed; it is discussed in comparison with the indirect method from Kirchhoff's law in [14].

In this paper we present a theory of photoluminescence of one-dimensional layered structures on the basis of the generalized form of Kirchhoff's law. It determines the spectral dependence of the photoluminescence intensity when the lifetime of excited states of emitting atoms, which we will term "emitting centers" (ECs) or simply "emitters", is long enough compared to the thermalization time of electrons participating in optical transitions and short compared to the energy redistribution time for the rest of the system ("slow" subsystem), so that the energy distribution stays the same while the spectrum is being measured. In this case, which is typical of (stationary) luminescence experiments, it is possible to use the concept of local thermodynamic equilibrium and introduce an effective temperature to describe the quasi-equilibrium distribution. As the condition of quasi-thermal equilibrium is sufficient for the generalized Kirchhoff's law to hold true, it characterizes not only general thermodynamic properties of the light-emitting systems but also the specificity of the emitting material. A similar approach is used to quantitatively describe luminescence spectra of very different systems including astrophysical objects [15–18] and is sometimes mentioned in the literature as the generalized Planck's law [19 and 20]. Also, there exists a well-known relation between the absorption and luminescence spectra called the van Roosbroeck–Shockley relation [21] (and also the Kennard-Stepanov relation [22 and 23]).

As is known, in the semi-classical theory of radiation the atom is treated as a quantum mechanical system while the electromagnetic field is described classically. However, to get the true value of the Einstein A coefficient for spontaneous emission one has to take into account both the radiation reaction field and vacuum field fluctuations [4]. Since the type of emitters in our theory plays no important role, this theory can be considered equally as classical and as semi-classical and, consequently, the question about the origin of spontaneous emission does not arise here.

The analytical expressions presented in this paper can be used in calculations of the PL spectra for multi-layered structures (which in many experimental situations can be considered as quasi-one-dimensional), in particular, from a 1D photonic crystal composed of the layers uniformly

doped with the emitting centers. The numerical calculation procedure using these expressions is much less cumbersome and more explicit compared to a commonly used method based on the Fermi's golden rule approach and the concept of the local density of optical states derived from the Green's function of the system [2, 24–26]. The last method, as is shown in the paper, is equivalent to the approach developed here. Its application is illustrated on the example of calculation of the IEF for a 1D photonic crystal composed of two types of layers for the case when the light emission is generated from only one type of layers. It is possible in this case to make a relatively simple analysis which helps reveal some features of the IEF such as its asymmetry about the center of a PBG and the evolution of the emission peaks with a change in the number of periods of the structure. On the whole, this theory is a development of the approach presented in [27] and differs from the latter and other theories of emission in periodic structures in giving an analytical expression for the emission intensity.

II. THE GENERALIZED KIRCHHOFF'S LAW FOR 1D LAYERED STRUCTURE

As a model system, we consider a 1D photonic crystal consisting of alternating plane layers, A and B, with thicknesses a and b and real values of the refractive indices n_a and n_b, respectively. The active (A) layers contain a large number of emitting centers (e.g., complexes of impurity atoms or ions with the nearest neighbour ions), differing, in general, in their rates of radiative (and non-radiative) transitions; we assume for simplicity that the concentration of ECs in each A layer is the same. In the present theory, the specific nature of such emitters is of no importance from the point of view of the general approach and is taken into account separately. It is partly due to the fact that the underlying Kirchhoff's law of thermal radiation is independent of the equilibrium-producing material and it is valid if the energy distribution of the excited states of the emitting centers is independent of frequency of the exciting laser beam. (Thus, the theory is applicable to transparent media and is not suitable, for instance, for microcavities with metallic walls, though the weak-coupling regime is fulfilled).

We start with the equation for the photoluminescence intensity for a one-layer structure [27 and 28]:

$$I(\omega) = \hbar\omega \exp(\mu/k_BT) N^0_{ph}(\omega) A'(\omega) \,. \qquad (1)$$

Here $N^0_{ph}(\omega)$ is the photon distribution function (which is approximately $\exp(-\hbar\omega/k_BT)$ at not too high temperatures, $k_BT \ll \hbar\omega$), the factor $\exp(\mu/k_BT)$ is due to a shift in the Boltzmann distribution function at quasi-equilibrium condition (owing to deviation from thermal equilibrium) and $A'(\omega)$ is the absorption coefficient defined as

$$A'(\omega) = 1 - |r(\omega)|^2 - |t(\omega)|^2 \,,$$

where $r(\omega)$ and $t(\omega)$ are the amplitude reflection and transmission coefficients of light at normal incidence; the prime on the function $A(\omega)$ denotes that absorption is very small, i.e. $A'(\omega) = \lim_{n''\to 0} A(\omega)$, where n'' is the imaginary part of the refractive index associated with the absorption of light by ECs. Hereafter we consider a layer-by-layer structure, so we define $A'_m(\omega)$ as the contribution to the absorption by the m-th layer of N-layer structure. As follows from the excitation conditions for luminescence we should disregard the reabsorption and re-emission effects and thus to keep only the first-order term in $n''_{EC}(\omega)$ in the Taylor series for $A'_m(\omega)$, where $n''_{EC}(\omega)$ is proportional to concentration of ECs, emitting at the frequency ω. It follows then that $A'_m(\omega)$ can be represented by

$$A'_m(\omega) = \phi_m(\omega) n''_{EC}(\omega) \,, \;\; \phi_m(\omega) = dA'_m(\omega)/dn'' \,. \quad (2)$$

Then the intensity of photoluminescence from the m-th A layer can be written in the form:

$$I_m(\omega) \propto \omega f_T(\omega) \phi_m(\omega) F_m(\omega_0) \,. \qquad (3)$$

This expression is obtained from Eqs. (1) and (2) by replacing $\exp(\mu/k_BT) N^0_{ph}(\omega) n''_{EC}(\omega)$ with a new distribution function, $f_T(\omega)$, which depends on the temperature T of the system.

Let us explain the meaning of the functions in Eq. (3). The function $f_T(\omega)$ is determined by the nature of ECs and the kind of the light-emitting material and thus is related to the bulk emission spectrum (in the absence of a quasi-standing wave resulting from the light reflection from two interfaces); it is calculated per unit volume or thickness of the layer [29]. The function $\phi_m(\omega)$ is determined exclusively in terms of parameters of the structure (in particular, it is dependent on the total number of layers) and is responsible for modification of the spectrum compared to that from a bulk material. The function $F_m(\omega_0)$ in Eq. (3) gives the relative intensity of the light absorbed in the m-th layer at the excitation frequency ω_0. In a rough approximation it has the form $\exp(-\alpha m)$, where α is proportional to the attenuation coefficient. A more exact expression for the function $F_m(\omega)$ and its connection to $\phi_m(\omega)$ will be given below.

The photoluminescence intensity $I_N(\omega)$ from the structure containing N active (A) layers is the sum of contributions: $I_N(\omega) = \sum_{m=1}^{N} I_m(\omega)$. In the case of a small value of the imaginary part of refractive index of the constituent materials at the frequency ω, one can set $A'_N(\omega) = \sum_m A'_m(\omega)$. Hence $\Phi_N(\omega) = \sum_m \phi_m(\omega)$ and, consequently, by neglecting the difference in values of $F_m(\omega_0)$ for different A layers, one gets

$$I_N(\omega) = \hbar\omega f_T(\omega) \Phi_N(\omega) \,, \qquad (4)$$

which as well as Eq. (3) we call the generalized Kirchhoff's law for a one-dimensional layered structure. (The equality sign in Eq. (4) means only that the distribution function $f_T(\omega)$ is appropriately normalized.)

If a 1D photonic crystal is terminated from one side with a plane interface between the material B and a medium with the refractive index n_0, so that the distance between two interfaces (of the three materials) is equal b', Eq. (4) should be multiplied by the factor $|\tau/(1-\varrho r_N e^{i\varphi_0})|^2$, where $\varrho=(n_b-n_0)/(n_b+n_0)$, $\tau=2n_b/(n_b+n_0)$ and $\varphi_0=(2b'-b)\omega n_b/c$.

Now we will describe in more detail the calculation procedure of the photoluminescence intensity from a 1D photonic crystal. We shall study the case of normal incidence of light on the structure from a medium with a refractive index n_b. It is useful to give the expressions for the amplitude reflection and transmission coefficients for the structure with an arbitrary number N of the A layers [30]:

$$r_N = r_1 \sin NQd/Z_N,\ \ t_N = t_1 \sin Qd/Z_N\,,$$

where r_1 and t_1 are the reflection and transmission coefficients for a single A layer defined as
$r_1 = 2ie^{i(\varphi_a+\varphi_b)} r \sin\varphi_a/\xi$ and $t_1 = e^{i(\varphi_a+\varphi_b)}(1-r^2)/\xi$.
The other notations used are:
$\varphi_a=\omega n_a a/c$, $\varphi_b=\omega n_b b/c$, $r=(n_a-n_b)/(n_a+n_b)$,
$t=2n_b/(n_a+n_b)$, $\xi=1-r^2e^{2i\varphi_a}$ and

$$Z_N(\omega) = \sin NQd - t_1 \sin(N-1)Qd\,, \qquad (5)$$

where the magnitude of the wave vector, Q, satisfies the equation

$$\cos Qd = \cos\varphi_a\cos\varphi_b - \frac{1}{2}\left(\frac{n_a}{n_b}+\frac{n_b}{n_a}\right)\sin\varphi_a\sin\varphi_b. \quad (6)$$

It is convenient to introduce $\eta_m = t_m/(1-r_m r_{N-m})$. By considering the energy flux density through the m-th A layer with the imaginary part of the refractive index n'', one can show that the function $F_m(\omega)$, which in the limit of $n''\to 0$ turns to $F'_m(\omega)\equiv\phi_m(\omega)n''$, can be written in the form

$$F_m(\omega) = |\eta_{m-1}|^2(1-|r_{N-m+1}|^2) - |\eta_m|^2(1-|r_{N-m}|^2)\,. \qquad (7)$$

This expression can be used for approximate calculation of the intensity of the pump, $F_m(\omega_0)$, at an arbitrary value of $n''(\omega_0)$. (The prime on the function $F_m(\omega)$ implies that $n''\to 0$.)

It is worth mentioning that if the emitting centers are contained not only in the A layers but also in the B layers, the calculation of emission intensity should be made by taking into account the contributions from both types of layers on the basis of the following expression:
$A'(\omega) = n''_a\Phi^{(a)}_N(\omega) + n''_b\tilde\Phi^{(b)}_N(\omega)$, where

$$\Phi^{(a)}_N(\omega) = \left(\frac{\partial A(\omega)}{\partial n''_a}\right)_{n''_b=0},\quad \tilde\Phi^{(b)}_N(\omega) = \left(\frac{\partial A(\omega)}{\partial n''_b}\right)_{n''_a=0}.$$

The function $\Phi^{(a)}_N(\omega)$ should be calculated in the limit $n''_a\to 0$ and it may be written in analogy with Eq. (2) as $\sum_m \phi^{(a)}_m(\omega)$, where the sum is over all of the A layers in the structure. The function $\tilde\Phi^{(b)}_N(\omega)$ is defined in an analogous way. With the above taken into consideration, Eqs. (3) and (4) can easily be generalized to the case of two types of active layers, A and B. In the following sections, for simplicity, we confine ourselves to the simplest case when only the A layers are luminescent (so that $n''_b=0$) and for the sake of shortness, instead of $\Phi^{(a)}_N(\omega)$, we will use the notation $\Phi_N(\omega)$, as earlier.

III. A GENERAL CALCULATION OF PHOTOLUMINESCENCE INTENSITY

In the weak-coupling approximation the emission intensity can be calculated by the rate equation for the excited state population (the number of emitting centers in the excited state) and is given by [26 and 31] $I(\omega)=P\kappa_r(\omega)/(\kappa_r(\omega)+\kappa_{nr})$, where P is the rate of excitation, and $\kappa_r(\omega)$ and $\kappa_{nr}(\omega)$ are the radiative and nonradiative decay rates for the transition from an excited state to the ground state. In the case of low quantum efficiency $\kappa_r \ll \kappa_{nr}$, so that $I(\omega)\approx P\kappa_r(\omega)/\kappa_{nr}$. In the simplest case P and κ_{nr} can be considered constant and, consequently, the spontaneous emission rate enhancement factor (the Purcell factor), $\gamma(\omega)\equiv\kappa_r(\omega)/\kappa^{(0)}_r(\omega)$, is approximately equal to $I(\omega)/I^{(0)}(\omega)$, where $I^{(0)}(\omega)$ and $I(\omega)$ are the emission intensities from a bulk sample (or in vacuum) and from the structure, respectively, and $\kappa^{(0)}_r(\omega)$ and $\kappa_r(\omega)$ are the corresponding radiative decay rates.

Let us introduce the ratio $\gamma_m(\omega)\equiv I_m(\omega)/I^{(0)}_1(\omega)$, where $I^{(0)}_1(\omega)$ is the intensity from a single A layer of the thickness a, if the surrounding medium has the same refractive index as the A layer, $n_b=n_a$. Making use of Eq. (2) at m=1, we find that

$$\Phi_1(\omega)\equiv\phi_1(\omega) = \frac{2(1-r^2)[(1+r^2)\varphi_a + r\sin 2\varphi_a]}{n_a(1-2r^2\cos 2\varphi_a + r^4)}. \quad (8)$$

In the absence of dielectric contrast this expression takes the form $\Phi^{(0)}_1(\omega)=2\omega a/c$, and from Eq. (3) without taking into account $F_m(\omega_0)$ one gets

$$\gamma_m(\omega) = c\phi_m(\omega)/(2a\omega) \qquad (9)$$

and the analogous quantity for the whole structure

$$\Gamma_N(\omega)\equiv I_N(\omega)/(NI^{(0)}_1(\omega)) = c\Phi_N(\omega)/(2Na\omega)\,, \quad (10)$$

which we call the spontaneous emission intensity enhancement factors. Evidently, the functions $\gamma_m(\omega)$ and $\Gamma_N(\omega)$ give the relative change in emission intensity for the m-th A layer and N-period structure, respectively. Hence, together with Eq. (4), one obtains the expression $I_N(\omega)\propto\omega^2 f_T(\omega)aN\Gamma_N(\omega)$. The function $\Gamma_N(\omega)$, as well as $\Phi_N(\omega)$, is expressed only in terms of the parameters of the photonic crystal and does not depend on the emission characteristics of the sources (the emitting centers).

Notice that to get the maximum value of the intensity of photoluminescence, $I_N(\omega)$, the frequency corresponding to the highest peak of the function $\Gamma_N(\omega)$ should coincide with the frequency of the emission spectrum maximum of the bulk material.

Using the generalized Kirchhoff's law, one can make a more exact calculation of the photoluminescence intensity, by taking into account the difference in the light absorption in different regions of the m-th active layer. We now note that the function $\phi_m(\omega)$ corresponds to the time-average power of the (monochromatic) electromagnetic field absorbed per unit volume in the m-th active layer, $P = (1/8\pi)\omega\varepsilon''|\mathbf{E}(\mathbf{r},\omega)|^2$, (see [32]) integrated over the thickness of the layer; in our case $\varepsilon'' = 2n_a n''$. In the case when a plane electromagnetic wave of the frequency ω is normally incident on the structure, we can represent $\phi_m(\omega)$ as $C\omega\int_{-a/2}^{a/2}|\mathcal{E}^{(m)}(\omega,z)|^2dz$, where the function $\mathcal{E}^{(m)}(\omega,z)$ describes the distribution of the electric field along the m-th active layer and C is a coefficient. Applying the generalized Kirchhoff's law to an infinitesimally thin layer and taking into account the last relation, after integrating over the thickness of the m-th A layer, we arrive at the following relationship:

$$I_m(\omega) \propto \omega^2 f_T(\omega)\int dz|\mathcal{E}^{(m)}(\omega_0,z)|^2|\mathcal{E}^{(m)}(\omega,z)|^2\,. \quad (11)$$

The electric field $\mathcal{E}^{(m)}(\omega,z)$ can be written as

$$\mathcal{E}^{(m)}(\omega,z) = \mathcal{F}_1^{(m)}(\omega)e^{ik_a z} + \mathcal{F}_2^{(m)}(\omega)e^{-ik_a z}\,, \quad (12)$$

where the z-coordinate is measured from the center of the m-th A layer, $k_a = \omega n_a/c$ and the functions $\mathcal{F}_1^{(m)}$ and $\mathcal{F}_2^{(m)}$ are $\mathcal{F}_1^{(m)} = e^{i(\varphi_a+\varphi_b)/2}(\eta_{m-1} + \eta_m r_{N-m} r e^{i\varphi_a})/\xi$, $\mathcal{F}_2^{(m)} = e^{i(\varphi_a+\varphi_b)/2}(\eta_{m-1} r e^{i\varphi_a} + \eta_m r_{N-m})/\xi$. The function $|\mathcal{E}^{(m)}(\omega_0,z)|^2$ is responsible for excitation of photoluminescence by incident light with a frequency ω_0.

The simplest way to get the coefficient of proportionality C is to compare Eq. (8) with the expression

$$\int_{-a/2}^{a/2}|\mathcal{E}^{(1)}(\omega,z)|^2dz = \frac{a[(1+r^2)\varphi_a + r\sin 2\varphi_a]}{\varphi_a(1-2r^2\cos 2\varphi_a + r^4)}\,, \quad (13)$$

which is obtained from Eq. (12) at $m = 1$; hence $C = (2/c)(1-r^2)$, where c is the speed of light in vacuum. The calculation of $\phi_m(\omega)$ with using Eq. (12) leads to

$$\phi_m(\omega) = \frac{2(1-r^2)\omega a}{c|\xi|^2}[g_1(|\eta_{m-1}|^2 + |\eta_m r_{N-m}|^2) + 2g_2 Re(\eta_m\eta^*_{m-1}r_{N-m})]\,, \quad (14)$$

$$g_1 = 1 + r^2 + r\frac{\sin 2\varphi_a}{\varphi_a}\,,\ \ g_2 = (1+r^2)\frac{\sin\varphi_a}{\varphi_a} + 2r\cos\varphi_a\,.$$

One can show that the calculation procedure described above is equivalent to the calculation of the light power generated by independent sources. (It is in accordance with the theory presented above, where the reabsorption and re-emission processes were ignored.) For this purpose one should express the intensity of radiation transmitted through the photonic crystal in terms of the amplitude of a plane electromagnetic wave coming from the plane $z = const$ (where z-axis is defined inside the m-th active layer with the origin in the layer center) and calculate the reflection and transmission coefficients taking into account all reflections and all re-reflections of electromagnetic waves from various interfaces of the layers of the structure. The resulting expression will have the same form as Eq. (11) in which $\mathcal{E}^{(m)}(\omega_0,z) = const$ and with $\mathcal{E}^{(m)}(\omega,z)$ proportional to Eq. (12).

In practice to calculate the PL intensity $I_N(\omega)$ of the structure with N active layers, one uses the photoluminescence spectrum $I_1^{(0)}(\omega)$ of a single active layer (of the thickness a_0). As follows from Eq. (11), the photoluminescence intensity under excitation at frequency ω_0 is

$$I_N(\omega) = I_1^{(0)}(\omega)\sum_{m=1}^{N}\int_{-a/2}^{a/2}J^{(m)}(\omega_0,\omega,z)dz \times\left(\int_{-a_0/2}^{a_0/2}J^{(1)}(\omega_0,\omega,z)dz\right)^{-1}\,, \quad (15)$$

where $J^{(m)}(\omega_0,\omega,z) = |\mathcal{E}^{(m)}(\omega_0,z)\mathcal{E}^{(m)}(\omega,z)|^2$. The equality sign in Eq. (15) implies that the power of excitation radiation in the case of N-period structure is exactly equal to that for the one-layer structure, otherwise it should be replaced by the sign of proportionality.

IV. THE PHOTOLUMINESCENCE SPECTRAL FUNCTION AND INTENSITY ENHANCEMENT FACTOR OF 1D PHOTONIC CRYSTAL

As is seen from Eq. (4) the main features of the luminescence spectra of 1D photonic crystal can be established from an analysis of the PL spectral function $\Phi_N(\omega)$ or, as discussed above, the emission intensity enhancement factor $\Gamma_N(\omega)$, see Eq. (10). Taking the sum over m from 1 to N on both sides of Eq. (2) and then calculating the derivative of $A'_N(\omega)$ one gets the following expression for the function $\Phi_N(\omega)$:

$$\Phi_N(\omega) = \frac{C_1 N + C_2\sin NQd}{(1-r^2)^2\sin^2 Qd + (2r\sin\varphi_a)^2\sin^2 NQd}\,, \quad (16)$$

where the functions C_1 and C_2 are given by

$$C_1 = [(1/n_b - n_b/n_a^2)\sin\varphi_a\sin\varphi_b + (2\sin\varphi_a\cos\varphi_b + (n_a/n_b + n_b/n_a)\sin\varphi_b\cos\varphi_a)\omega a/c] (1-r^2)[r^2\sin(\varphi_a-\varphi_b) + \sin(\varphi_a+\varphi_b)]\,,$$

$$C_2 = B_0\sin NQd + B_1\sin(N-1)Qd + B_2\sin(N-2)Qd - C_1(\sin NQd + \cos NQd\cot Qd)\,,$$

$$B_0 = 4[rt\sin 2\varphi_a/(n_a+n_b) + r^2(1-r^2)(\omega a/c)]\,,$$

$B_1 = -2(1-r^2)[3r^2\cos(\varphi_b-\varphi_a) - \cos(\varphi_a+\varphi_b)](\omega a/c)$
$- 8rt\sin\varphi_a\cos\varphi_b/(n_a+n_b)$,

$$B_2 = -2(1-r^2)^2(\omega a/c)\,.$$

When $N = 1$ this equation reduces to Eq. (8). It follows also from Eq. (16) that in the absence of dielectric contrast of the constituent materials (A and B) $\Phi_N^{(0)}(\omega) = 2N\omega a/c = N\Phi_1^{(0)}(\omega)$. In the long wavelength limit, at $\omega \to 0$, Eq. (16) converts to $2Nan_a\omega/(cn_b)$.

In the most interesting case, when $N \gg 1$, Eq. (16) is greatly simplified and takes the form

$$\Phi_N(\omega) \approx \frac{C_1(N - \sin NQd\cos NQd\cot Qd)}{(1-r^2)^2\sin^2 Qd + (2r\sin\varphi_a)^2\sin^2 NQd}\,. \tag{17}$$

This expression is a good approximation in the frequency region where the values of $C_1(\omega)$ are not too small (see the case $C_1 = 0$ below). A further simplification of the expression for $\Phi_N(\omega)$ can be made by setting in Eq. (16) $C_2 = 0$, which is valid for frequencies not too close to a PBG edge, where the condition $|\cot Qd\sin 2NQd| \ll 2N$ is satisfied; consequently, the numerator of Eq. (17) is equal to C_1N. At the Brillouin zone center ($Q = 0$) and at the Brillouin zone edge ($Q = \pi/d$) the function $\Phi_N(\omega)$ becomes $\Phi_N^{(BZ)} =$

$$\frac{2C_1N^3 + 3(B_0 \pm B_1 + B_2 - C_1)N^2 + (C_1 \mp 3B_1 - 6B_2)N}{3[(2Nr\sin\varphi_a)^2 + (1-r^2)^2]}$$

where the upper sign refers to $Q = 0$ and the lower sign refers to $Q = \pi/d$. The expression for $\Phi_N^{(BZ)}$ shows that for a sufficiently large number N of the layers ($N \gg 1$), approximately, $\Phi_N^{(BZ)} \propto N$.

As an example, Fig. 1 shows the IEF (curve 1) as a function of the wavelength λ for a distributed Bragg reflector (DBR) with $N = 10$ active (A) layers, the transmission spectrum (curve 2) calculated in the absence of absorption and also the function $C_1(\lambda)$ (curve 3). As seen from the figure, curve 1 is essentially asymmetric and has a set of peaks in two band regions, with the highest peaks being near the PBG edges. In the region of large wavelengths there are several spectral peaks, which with increasing the wavelength become lower and wider; an analogous situation occurs in the region on the opposite side of the PBG. Such a picture is typical of 1D photonic crystal; it is also observed when the emitting centers are uniformly distributed in the B layers or in both types of layers.

As follows from Eq. (16), the PL spectral function $\Phi_N(\omega)$ can be written as $P_N(\omega)/|\xi Z_N(\omega)|^2$, where $P_N(\omega) = C_1N + C_2\sin NQd$, therefore the peaks of the function $\Phi_N(\omega)$ and, consequently, $\Gamma_N(\omega)$, are located around the real values, ω_j', of the complex eigenfrequencies $\omega_j = \omega_j' + i\omega_j''$ which can be found from the equation $Z_N(\omega_j) = 0$, see Eq. (5). When absorption can be neglected the transmission coefficient in the band region is $T(\omega) = |t_N(\omega)|^2 = (1-r^2)^2\sin^2 Qd/|\xi Z_N(\omega)|^2$. As the denominator of the function $T(\omega)$ is the same as for $\Gamma_N(\omega)$, while the function $\sin^2 Qd$ is rather smooth, the transmission peaks are located around ω_j' as well and are slightly shifted relative to the peaks of the function $\Gamma_N(\omega)$, see Fig. 1. Thus, the positions of peaks of the IEF, $\Gamma_N(\omega)$, are close to those at which $T(\omega) = 1$ and, consequently, the wave numbers corresponding to the local maxima of $\Gamma_N(\omega)$ are $Q_jd = \pi j/N + \delta_j$, $|\delta_j| \ll 1$, where j are integers and the frequencies ω_j satisfy Eq. (6) with $Q = Q_j$. Disregarding the value of $N\delta_j$, which for the peaks nearest to the PBG is $|N\delta_j| \ll 1$, one gets from Eq. (17)

$$\Phi_N(\omega_j) \approx \frac{C_1(\omega_j)N}{(1-r^2)^2\sin^2(\pi j/N)}\,. \tag{18}$$

Upon moving away from a PBG edge and passing successive values of ω_j, the denominator (the squared sine) increases in a monotonous way and after that monotonically decreases when approaching to another PBG. A more exact consideration shows that when moving away

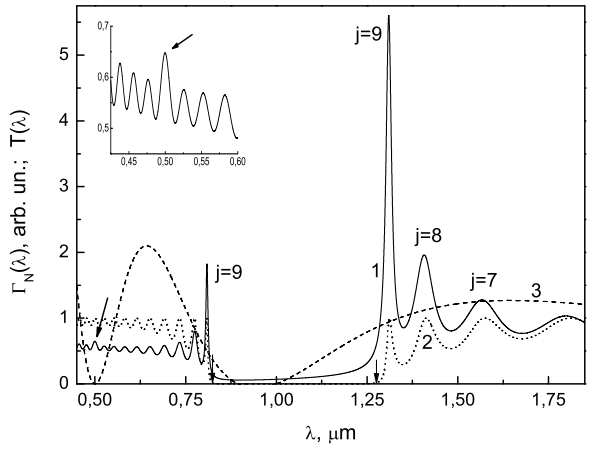

FIG. 1. The intensity enhancement factor, $\Gamma_N(\lambda)$, (curve 1) and transmission coefficient, $T(\lambda)$, (curve 2) that has a correlation with the IEF in the position of the spectral peaks. The graph of the function $\Gamma_N(\lambda)$ is plotted by using Eqs. (10) and (16) and coincides with that plotted by using Eqs. (10) and (17) except for a small region around $\lambda_c = 0.5\,\mu m$, where Eq. (17) is not valid. The numbers $j = 9, 8, ...$ in the figure indicate the corresponding spectral peaks. The curve 3 shows the function $C_1(\omega)$, which is equal to zero at $\lambda_c = 0.5\,\mu m$ (at which the second PBG collapses). The vertical arrows indicate the edges of the first PBG. The inclined arrow shows a distinguished peak at the wavelength of $\lambda_c = 0.5\,\mu m$, see also the inset of the figure. Calculated for a DBR with $N = 10$ periods, the thicknesses $a = \bar\lambda/(4n_a) = 125$ nm, $b = \bar\lambda/(4n_b) = 250$ nm and refractive indices $n_a = 2$, $n_b = 1$ of the layers A and B, respectively; the tuning wavelength $\bar\lambda = 1000$ nm.

from the PBG edge the values of δ_j can increase and should be taken into account, but qualitatively the situation remains quite similar; since on the scale of the distance b etween the neighbouring peaks the function $C_1(\omega)$ changes relatively slowly compared to $\sin^2 Q(\omega)d$, the peaks of the function $\Phi_N(\omega)$ and, consequently, $\Gamma_N(\omega)$ are getting lower. The highest peaks correspond to $j = 1$ (at the PBG edge $Q = 0$) and $j = N-1$ (at the edge $Q = \pi/d$). This explains why enhancement of the PL intensity occurs predominantly in the band region in the vicinity of the band-gap edge, see, e.g., [33]. It is obvious from Eq. (18) that if $j \ll N$ or $j \lesssim N$ (in the limit $N \gg 1$) $\Phi_N(\omega_j) \propto N^3$, so that with increasing the number of periods, N, the peaks of the function $\Phi_N(\omega)$ increase and approach to the PBG edges, and their number increases as well (in accordance with Eq. (5) and the simplified formula $Q_j d \approx \pi j/N$).

Another feature of the functions $\Phi_N(\omega)$ and $\Gamma_N(\omega)$ is their asymmetry relative to the PBG center. It can be easily explained with the help of Eq. (18) and expression for the function $C_1(\omega)$. Let us denote by ω_{j-} and ω_{j+} the frequencies corresponding to the peaks of the function $\Gamma_N(\omega)$ on different sides of a PBG. Evidently, $C_1(\omega_{j-})$ and $C_1(\omega_{j+})$ can take substantially different values that leads to an asymmetry in the height of the peaks with the same number j. In the example considered above (see Fig. 1) the PBG edges satisfy the condition $Qd = \pi$, consequently the peaks of $\Gamma_N(\omega)$ nearest to the PBG correspond to the integers $j = 9, 8, ...$ It follows from Eq. (18) that $\Phi_N(\omega_{j+})/\Phi_N(\omega_{j-}) \approx C_1(\omega_{j+})/C_1(\omega_{j-})$, therefore the ratio $\zeta(j) \equiv \Gamma_N(\omega_{j+})/\Gamma_N(\omega_{j-}) \approx \omega_{j-}C_1(\omega_{j+})/(\omega_{j+}C_1(\omega_{j-})) \equiv \tilde{\zeta}(j)$. The calculation gives the following values: $\zeta(j = 9) = 3.075$, $\tilde{\zeta}(j = 9) = 3.045$ and $\zeta(j = 8) = 2.439$, $\tilde{\zeta}(j = 8) = 2.408$, which verifies the applicability of Eq. (18). The analysis of Eq. (17) allows one to determine approximate values of the local minima of the PL spectral function. They correspond to the wave numbers $Q_k d = \pi(2k+1)/(2N)$, where $k = 1, ...N-2$, hence $\Phi_N(\omega_k) \approx$

$$\frac{C_1(\omega_k)N}{(1-r^2)^2 \sin^2(\pi(2k+1)/(2N)) + (2r\sin(\omega_k n_a a/c))^2}.$$

This expression also explains the asymmetry of the PL spectral function and, as a consequence, of the IEF.

The value of the function $C_1(\omega)$ changes considerably on the scale of the distance between the edges of PBGs, therefore it essentially determines the value of the IEF at a given frequency, in particular for frequencies close to a PBG edge, where the values of $\Phi_N(\omega_j)$ and $\Gamma_N(\omega_j)$ can be large, see Eq. (18). Therefore, by choosing the appropriate parameters and, thus, "governing" the function $C_1(\omega)$ one can achive either an anomalously large enhancement of the emission intensity or its moderate suppression. However, as follows from the analysis of the function $C_1(\omega)$, for frequencies in a photonic band the inequality $C_1(\omega) > 0$ is always satisfied. This means that in the case of a 1D photonic crystal (without a defect) the light emission in the regime $I_N \propto N$ at a PBG edge (because $\Phi_N^{(BZ)} \propto N$) and $I_N \propto N^3$ at the spectral peak frequency ω_j (because $\Phi_N \propto N^3$) cannot be suppressed completely, but can only be decreased due to a relatively small value of $C_1(\omega_j)$.

There is a special case when at the frequency ω_c the photonic band-gap vanishes and, as the analysis shows, $C_1(\omega_c) = 0$. It is worthwhile to notice that at this frequency the function $\Phi_N(\omega)$ and, consequently, $\Gamma_N(\omega)$ has a local maximum. In the case considered in Fig. 1 the corresponding peak appears at the wavelength $\lambda_c = 0.5\,\mu m$. This peak is higher than the neighbouring ones, because at the wavelength λ_c all of the functions $\phi_m(\omega)$, where $m = 1, 2, ...N$, have local maxima (see inset of Fig. 2). A quantitative description of this effect can be made by using Eqs. (14) and (16) and will be given elsewhere. The qualitative explanation is that as the PBG is getting narrower two spectral peaks adjoining the PBG edges essentially evolve and at the frequency ω_c join to form a single peak. Moreover, since in the case of a 1D photonic crystal the topology of the band structure for propagation of electromagnetic waves is determined by the number of photonic band-gaps, one can expect that in energy spectrum at the point where the topology changes (at the frequency at which a PBG collapses) some peculiarity will arise. This, indeed, occurs and manifests itself as a local maximum of the PL spectral function $\Phi_N(\omega)$, which determines the power of the electromagnetic radiation absorbed per unit volume.

We now briefly consider the behavior of the functions

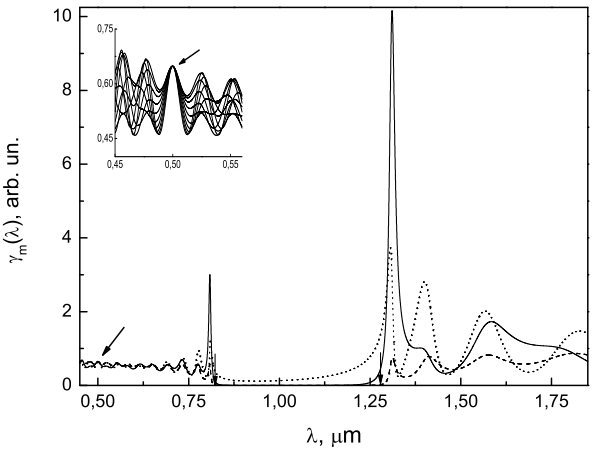

FIG. 2. The partial IEFs, $\gamma_m(\lambda)$, for the layers $m = 2$ (dotted line), $m = 6$ (solid line) and $m = 10$ (dashed line). The vertical arrows indicate the PBG edges. The inset shows a set of functions $\gamma_m(\omega)$, where $m = 1, 2, ...10$, which at the wavelength $\lambda_c = 0.5\,\mu m$ have the same local maximum value (the peak is indicated by arrow). Calculated for the same parameters as in Fig. 1.

$\gamma_m(\omega)$, which are the (partial) intensity enhancement factors for different emitting layers of the photonic crystal. Figure 2 shows the partial IEFs calculated by using Eqs. (9) and (14) for the layers $m = 2, 6$ and 10 (see caption to Fig. 2). As seen from the figure, the central and first nearest layers give the largest contributions to the total intensity (at different wavelengths), while the remote layers emit relatively weakly. This behavior of the functions $\gamma_m(\omega)$ can be explained from the analysis of Eq. (14). Qualitatively, the electromagnetic radiation from a remote layer experiences strong reflection from the rest of the structure, while the transmittance of the radiation coming from the first nearest layer at some wavelengths can be sufficiently high. The highest peaks of the functions $\gamma_m(\omega)$ near the PBG edges for the central layers (m =5 and 6) are due to some kind of microcavity effect, see Fig. 2. In general, as shown in the previous section, the frequency dependence of the IEF is associated with the distribution of electric field modes in the photonic crystal structure.

V. DISCUSSION (CONNECTION TO THE GREEN'S FUNCTION METHOD)

Now we briefly discuss how the theory presented above is connected with the most commonly used theory of light emission from microstructures. As is known, there are two different ways to describe the emission process and calculate intensity of the emitted light, namely, classical and quantum approaches; their equivalence and difference have been discussed in detail in many papers and books, e.g., see [2, 4, and 34]. In the classical approach the electromagnetic power is due to emitting dipoles and is given by

$$\frac{dW}{dt} \propto \omega^3 |\mathbf{d}|^2 \left\langle \mathbf{e}_d \cdot Im[\mathbf{G}(\mathbf{r}, \mathbf{r}, \omega)] \cdot \mathbf{e}_d \right\rangle \ , \qquad (19)$$

where $\mathbf{d}$ is the dipole moment oriented along the unit vector $\mathbf{e}_d$ and located at the point $\mathbf{r}$, $\mathbf{G}(\mathbf{r}, \mathbf{r}', \omega)$ is a dyadic Green's function [35] of the considered system, and the angle brackets denote an average over all possible dipole orientations. (The emitting centers are modelled as point dipoles with randomly oriented dipole moments.) In the case of uniform and isotropic distribution of dipole moments in an active (A) layer the average in Eq. (19) can be expressed through the trace of the imaginary part of the dyadic Green's function [2]. In this connection we study non-polarized radiation and consider the source (electric current density) and response (electric or magnetic field) as scalar functions; hence, the corresponding Green's function is also a scalar function. Thus, by considering that dipoles are polarized in one plane, in the case of a one-layer structure one should take 1D scalar Green's function, calculate its imaginary part at the position of an emitting center for coincident emission and observation points, $z = z'$, and then integrate over the layer thickness.

One-dimensional scalar Green's function, $G(z, z', \omega)$, defined for the points z and z' of a uniform layer with the thickness a (the both coordinates, z and z', are measured from the center of the layer in the same direction) satisfies the equation

$$(d^2/dz^2 + k_0^2 \varepsilon(z)) G(z, z', \omega) = -\delta(z, z')$$

and for $|z'| \le a/2$ is [36]:

$$G(z, z', \omega) = \frac{i}{2k_a} [e^{ik_a|z-z'|} + \frac{2re^{i\varphi_a}[\cos(k_a(z+z')) + re^{i\varphi_a}\cos(k_a(z-z'))]}{1 - r^2 e^{2i\varphi_a}}] \qquad (20)$$

One can show that

$$\int_{-a/2}^{a/2} ImG(z, z, \omega) dz = \frac{a(1-r^2)[(1+r^2)\varphi_a + r\sin 2\varphi_a]}{2k_a\varphi_a(1 - 2r^2\cos 2\varphi_a + r^4)}.$$

This expression is different from the function $\Phi_1(\omega)$ only by a factor of ω^{-2} and a constant, see Eq. (8) (and also by a factor of ω^{-1} from Eq. (13)). Hence, the emission intensity from a single A layer, $I_1(\omega) \propto \omega f_T(\omega)\Phi_1(\omega)$, is

$$I_1(\omega) \propto \omega^3 f_T(\omega) \int_{-a/2}^{a/2} ImG(z, z, \omega) dz \ ,$$

which is in accordance with Eq. (19), as $f_T(\omega)$ is the population distribution function. This consideration, for the sake of shortness and clearness, has been given for a one-layer structure without generalizing on the N-period structure.

In the quantum approach in the case of the weak-coupling regime and low quantum efficiency [26] the rate of direct radiative transitions is given by the Fermi's golden rule [34]. As is shown in [24], in this case the emission rate is proportional to the local density of states, $\rho(\mathbf{r}, \mathbf{e}_d, \omega)$, at the position of the emitting center: $\gamma_{rad}(\mathbf{r}) \propto \omega |\mathbf{d}|^2 \rho(\mathbf{r}, \mathbf{e_d}, \omega)$. The LDOS in turn is proportional to the imaginary part of the dyadic Green's function and calculated for the direction given by the orientation $\mathbf{e}_d$: $\rho(\mathbf{r}, \mathbf{e}_d, \omega) \propto \omega(\mathbf{e}_d \cdot Im[\mathbf{G}(\mathbf{r}, \mathbf{r}, \omega)] \cdot \mathbf{e}_d)$. Thus, the calculation of emission intensity based on Eq. (19) and with using 1D Green's function given by Eq. (20) reduces to the calculation on the basis of the generalized Kirchhoff's law, see Eqs. (3) and (4). This correspondence occurs because the generalized Kirchhoff's law stated in the paper is valid for a light-emitting medium with a real dielectric function, in which case one can use the conventional concept of the LDOS.

VI. CONCLUSION

In conclusion, we have stated the generalized Kirchhoff's law for one-dimensional layered structures, which is applicable to the calculation of the photoluminescence

spectra if local thermodynamic equilibrium holds between the matter and radiation. The overlapping integrals of intensity distributions of the photonic crystal modes and pump excitation modes are expressed in terms of the amplitude reflection and transmission coefficients, which is convenient for numerical calculations and qualitative analysis. The developed approach is also convenient to obtain the expression for the spontaneous emission intensity enhancement factor whose analysis has allowed us to establish some features of the modification of the light emission in the case of 1D photonic crystals, in particular, the enhancement of emission intensity at the photonic band edges. In general, the proposed approach provides the physical basis for luminescence engineering of 1D layered structures, in particular, photonic crystals and microcavities.

ACKNOWLEDGMENTS

The author thanks E. L. Ivchenko and A. B. Pevtsov for helpful discussions and M. M. Glazov for making valuable comments on the manuscript.

* mikle.voronov@coherent.ioffe.ru

[1] K. Busch, S. Lolkes, R. B. Wehrspohn, H. Foll, *Photonic crystals: advances in design, fabrication and characterization*, Wiley-VCH (1994).

[2] L. Novotny and B. Hecht, *Principles of nano-optics*, Cambridge University Press (2006).

[3] G. S. Agarwal, J. of Mod. Opt. **45**, 449 (1998).

[4] P. W. Milonni, *The quantum vacuum: an introduction to quantum electrodynamics*, Academic Press (1993).

[5] E. M. Purcell, Phys. Rev. **69**, 681 (1946).

[6] S. M. Dutra and P. L. Knight, Phys. Rev. A **53**, 3587 (1996).

[7] A. S. Sanchez and P. Halevi, Phys. Rev. E **72**, 056609 (2005).

[8] H. J. W. M. Hoekstra, H. B. H. Elrofai, Phys. Rev. E **71**, 046609 (2005).

[9] S. E. Han, Phys. Rev. B **80**, 155108 (2009).

[10] K. Kuroda, T. Sawada, T. Kuroda, K. Watanabe, K. Sakoda, J. Opt. Soc. Am. B **27**, 010045 (2010).

[11] J. M. Bendickson, J. P. Dowling, M. Scalora, Phys. Rev. E, **53**, 4107 (1996).

[12] A. Settimi, S. Severini, N. Mattiucci, C. Sibilia, M. Centini, G. D'Aguanno, M. Bertolotti, M. Scalora, M. Bloemer, C. M. Bowden, Phys. Rev. E **68**, 026614 (2003).

[13] I. S. Fogel, J. M. Bendickson, M. D. Tocci, M. J. Bloemer, M. Scalora, C. M. Bowden, J. P. Dowling, Pure Appl. Opt. **7**, 393 (1998).

[14] C. M. Cornelius, J. P. Dowling, Phys. Rev. A **59**, 4736 (1999).

[15] P. Würfel, J. Phys. C: Solid State Phys., **15**, 3967 (1982).

[16] H. Ries, W. Spirkl, **38**, 39 (1995).

[17] L. Ferraioli, P. Maddalena, E. Massera, A. Parretta, M. A. Green, A. Wang, J. Zhao, Appl. Phys. Lett. **85**, 2484 (2004).

[18] E. A. Sharkov, *Passive Microwave Remote Sensing of the Earth: Physical Foundations*, Springer/PRAXIS (2003).

[19] K. Henneberger, Phys. Stat. Solidi B **246**, 283 (2009).

[20] E. Daub and P. Würfel, Phys. Rev. Lett. **74**, 1020 (1995).

[21] W. van Roosbroeck, W. Shockley, Phys. Rev. **94**, 1558 (1954).

[22] E. H. Kennard, Phys. Rev. **11**, 29 (1918).

[23] B. I. Stepanov, Dokl. Akad. Nauk SSSR **112**, 839 (1957) [Sov. Phys. Dokl. **2**, 81 (1957)].

[24] R. Sprik, B. A. van Tiggelen, A. Lagendijk, Europhys. Lett. **35**, 265 (1996).

[25] E. Yeganegi, A. Lagendijk, A. P. Mosk, W. L. Vos, Phys. Rev. B **89**, 045123 (2014).

[26] W. L. Vos, L. A. Woldering, arXiv:1504.06803v1 [quant-ph], (2015).

[27] M. M. Voronov, E. L. Ivchenko, M. V. Erementchouk, L. I. Deych, A. A. Lisyansky, J. Lumin. **125**, 112 (2007).

[28] L. I. Deych, M. V. Erementchouk, A. A. Lisyansky, E. L. Ivchenko, M. M. Voronov, Phys. Rev. B **76**, 075350 (2007).

[29] The calculation of the function $f_T(\omega)$ is a separate problem; for example, for many disordered materials the function $f_T(\omega)$ can be approximated by a slightly a symmetric Gaussian curve with a steeper slope on the side of high frequencies [see D. J. Dunstan, F. Boulitrop, Phys. Rev. B **30**, 5945 (1984)]. Therefore the function $\omega^2 f_T(\omega)$, which accounts for the emission spectrum of a bulk sample (a dielectrically homogeneous medium), becomes fairly symmetric that is sometimes observed in photoluminescence experiments [see F. Giorgis, P. Mandracci, L. Dal Negro, C. Mazzoleni, L. Pavesi, J. Non-Cryst. Sol. **266**, 588 (2000)]. (It is one of the possible reasons for the appearance of symmetric PL spectra.)

[30] E. L. Ivchenko, *Optical spectroscopy of semiconductor nanostructures*, Alpha Science International, Harrow, UK, (2005).

[31] A. F. Koenderink, L. Bechger, A. Lagendijk, W. L. Vos, Phys. Stat. Sol. (a) **197**, 648 (2003).

[32] L. D. Landau, E. M. Lifshitz, *Electrodynamics of Continuous Media*, Pergamon Press (1984).

[33] A. V. Medvedev, N. A. Feoktistov, A. B. Pevtsov, V. G. Golubev, Semiconductors, **39**, 1356 (2005).

[34] R. Loudon, *The quantum theory of light*, Oxford University Press (2000).

[35] Chen-To Tai, *Dyadic Green functions in electromagnetic theory*, IEEE Press (1994).

[36] E. L. Ivchenko, V. P. Kochereshko, A. V. Platonov, D. R. Yakovlev, A. Waag, W. Ossau, G. Landwehr, Phys. Solid State **39**, 1852 (1997).